



## SSC8120GS6

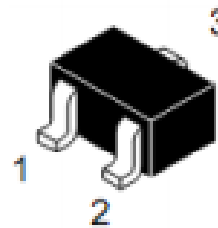
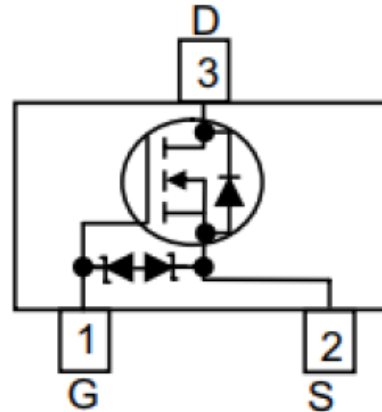
### N-Channel Enhancement Mode MOSFET

#### ➤ Features

VDS	VGS	R <sub>DS(on)</sub> Typ.	I <sub>D</sub>	ESD
20V	±12V	310mR@4V5	1.2A	1.2K
		490mR@2V5		
		850mR@1V8		

#### ➤ Pin configuration

Top view



SOT23

#### ➤ Description

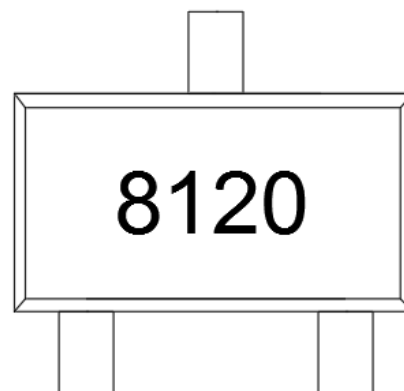
This device is a N-Channel enhancement mode MOSFET which is produced with high cell density and DMOS trench technology. This device particularly suits low voltage applications, especially for battery powered circuits, the tiny and thin outline saves PCB consumption.

#### ➤ Applications

- Load Switch
- Portable Devices
- DCDC conversion

#### ➤ Ordering Information

Device	Package	Shipping
SSC8120GS6	SOT23	3000/Reel



Marking



➤ **Absolute Maximum Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain-to-Source Voltage	20	V
$V_{GSS}$	Gate-to-Source Voltage	$\pm 12$	V
$I_D$	Continuous Drain Current	1.2	A
$I_{DM}$	Pulsed Drain Current	3	A
$P_D$	Power Dissipation	0.25	W
$T_J$	Operation junction temperature	-55 to 150	$^{\circ}\text{C}$
$T_{STG}$	Storage temperature range	-55 to 150	$^{\circ}\text{C}$

➤ **Thermal Resistance Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance		499	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance		299	

➤ **Electronics Characteristics**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu\text{A}$	20			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.35	0.6	1	V
$R_{DS(on)}$	Drain-Source On- Resistance	$V_{GS}=4.5V, I_D=0.5A$		310	450	mR
		$V_{GS}=2.5V, I_D=0.5A$		490	765	
		$V_{GS}=1.8V, I_D=0.35A$		850	1300	

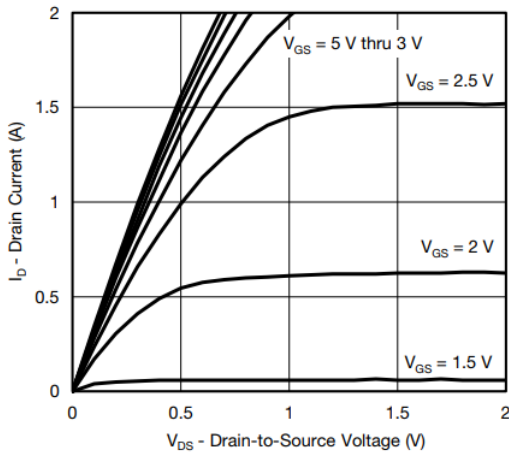


Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=16V, V_{GS}=0V$			1	$\mu A$
$I_{GSS}$	Gate-Source leak current	$V_{GS}=\pm 12V, V_{DS}=0V$			$\pm 10$	nA
$G_{FS}$	Forward Transconductance	$V_{DS}=5V, I_D=0.5A$		11		S
$V_{SD}$	Forward Voltage	$V_{GS}=0V, I_S=0.11A$		0.7	1.3	V

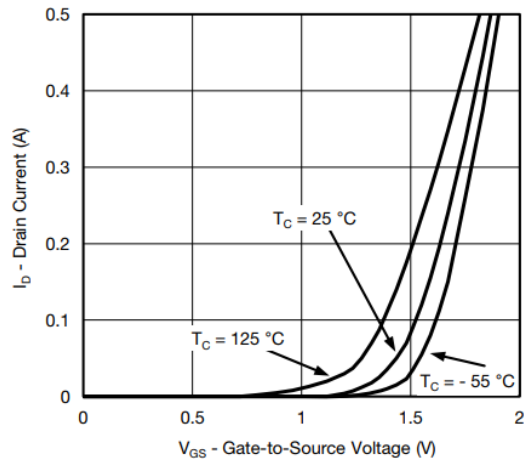
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$C_{iss}$	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $F=1MHz$		110		pF
$C_{oss}$	Output Capacitance			15		
$C_{rss}$	Reverse Transfer Capacitance			12		
$T_{D(ON)}$	Turn-on delay time	$V_{GS}=4.5V,$ $V_{DS}=5V, R_G=6R, I_D=0.3A$			5	ns
$T_{D(OFF)}$	Turn-off delay time				26	



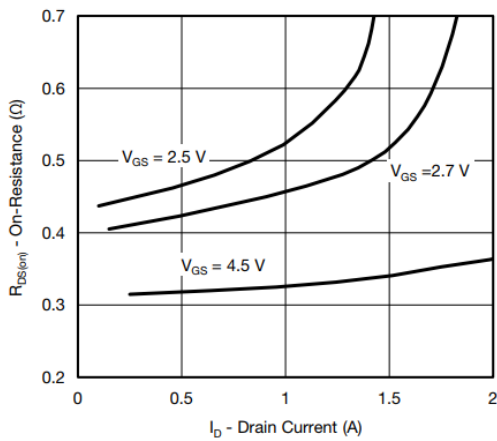
➤ Typical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)



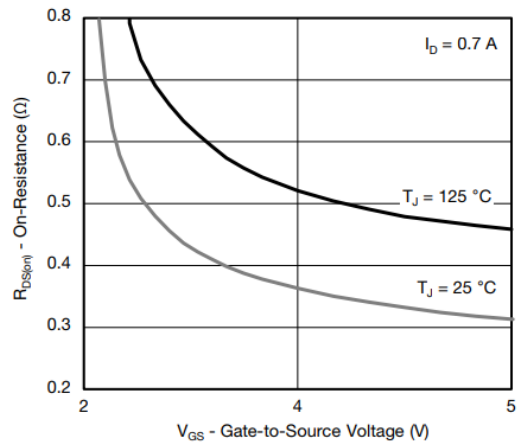
Output Characteristics



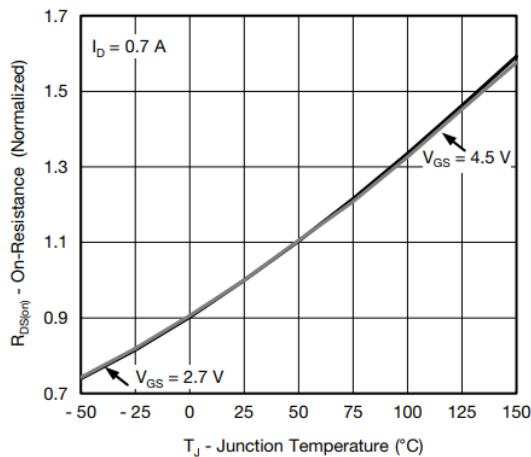
Transfer Characteristics



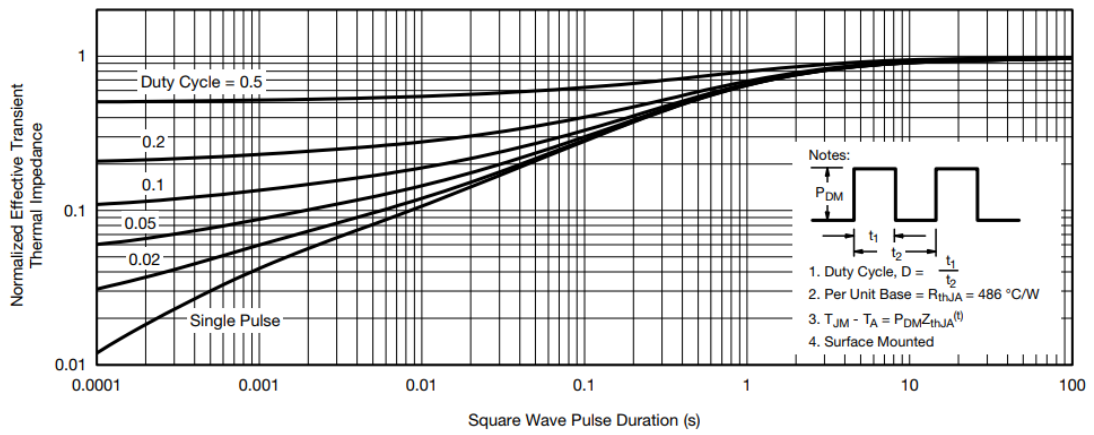
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage



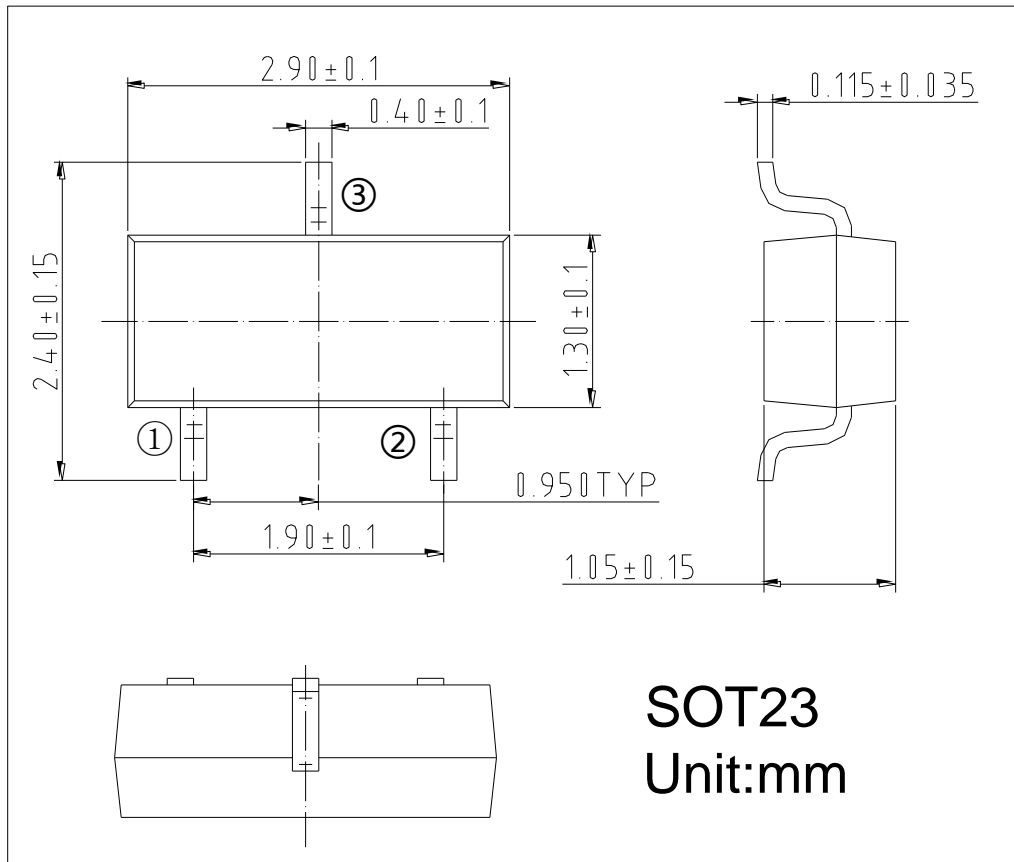
On-Resistance vs. Junction Temperature



Normalized Thermal Transient Impedance, Junction-to-Ambient



➤ Package Information



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